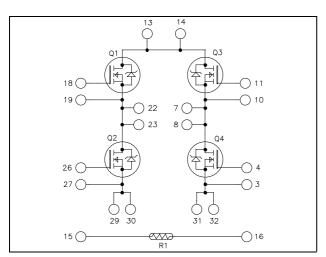
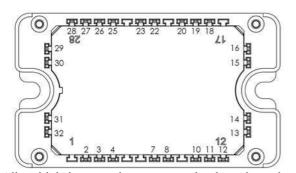


Full - Bridge MOSFET Power Module





All multiple inputs and outputs must be shorted together Example: 13/14; 29/30; 22/23 ...

$$\begin{split} V_{DSS} &= 500 V \\ R_{DSon} &= 65 m \Omega \text{ typ @ Tj} = 25^{\circ} C \\ I_{D} &= 51 A \text{ @ Tc} = 25^{\circ} C \end{split}$$

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

All ratings @ $T_i = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter Parameter		Max ratings	Unit
V_{DSS}	Drain - Source Voltage		500	V
Ţ	T	$T_c = 25^{\circ}C$	51	
I_D	Continuous Drain Current	$T_c = 80^{\circ}C$	38	A
I_{DM}	Pulsed Drain current	204		
V_{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		78	mΩ
P_D	Power Dissipation	390	W	
I_{AR}	Avalanche current (repetitive and non repetitive)		51	A
EAR	Repetitive Avalanche Energy		50	I
E_{AS}	Single Pulse Avalanche Energy		3000	mJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$			100	μΑ
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 25.5A$		65	78	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 2.5 \text{mA}$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{V}$			±150	nA

Dynamic Characteristics

•	Characteristic	Test Conditions	Min	Typ	Max	Unit
C _{iss}	Input Capacitance		171111	7000	with	Опи
Coss	Output Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$		1400		рF
C _{rss}	Reverse Transfer Capacitance	f = 1MHz		90		pr.
Qg	Total gate Charge			140		
Qgs	Gate – Source Charge	$V_{GS} = 10V$ $V_{Bus} = 250V$		40		nC
Q_{gd}	Gate – Drain Charge	$I_D = 51A$		70		
T _{d(on)}	Turn-on Delay Time	Inductive switching @ 125°C		21		
Tr	Rise Time	$V_{GS} = 15V$		38		
T _{d(off)}	Turn-off Delay Time	$V_{\text{Bus}} = 333 \text{V}$ $I_{\text{D}} = 51 \text{A}$		75		ns
T_{f}	Fall Time	$R_G = 3\Omega$		93		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		1035		_
E _{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 51A, R_G = 3\Omega$		845		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		1556		_
E_{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 51A, R_G = 3\Omega$		1013		μJ
R_{thJC}	Junction to Case Thermal Resistan	ce			0.32	°C/W

Source - Drain diode ratings and characteristics

	- Diam diode ratings and tha			14.	T	17	T T •4
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I_S	Continuous Source current		$Tc = 25^{\circ}C$			51	A
	(Body diode)		$Tc = 80^{\circ}C$			38	
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -51A$	1			1.3	V
dv/dt	Peak Diode Recovery					15	V/ns
t_{rr}	Daviana Dagayany Tima		$T_j = 25$ °C			270	***
	Reverse Recovery Time	$I_S = -51A$ $V_R = 333V$	$T_j = 125$ °C			540	ns
Qrr	Davarea Dagayawi Charea	$di_{S}/dt = 100A/\mu s$	$T_j = 25$ °C		2.6		
	Reverse Recovery Charge		$T_j = 125$ °C		9.6		μС

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

 $I_{S} \leq \text{--} 51 A \qquad di/dt \leq 700 A/\mu s \qquad V_{R} \leq V_{DSS} \qquad T_{j} \leq 150^{\circ} C$



Thermal and package characteristics

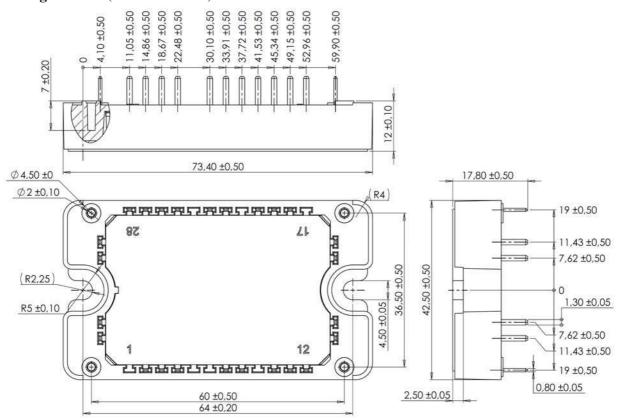
Symbol	l Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
$T_{\rm J}$	Operating junction temperature range			-40	150	
T_{JOP}	Recommended junction temperature under switching conditions			-40	T _J max - 25	°C
T_{STG}	Storage Temperature Range			-40	125	
$T_{\rm C}$	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink M4		2	3	N.m
Wt	Package Weight				110	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$	98.15 K		3952		K
$\Delta B/B$		$T_C=100$ °C		4		%

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \begin{array}{l} \text{T: Thermistor temperature} \\ R_T: \text{ Thermistor value at T} \end{array}$$

Package outline (dimensions in mm)

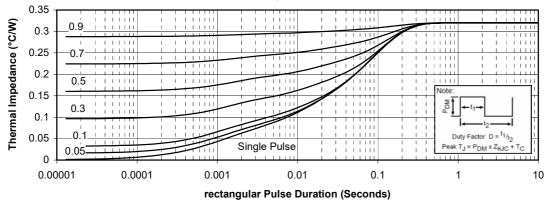


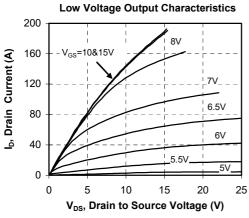
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

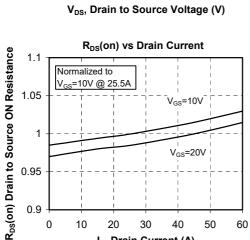


Typical Performance Curve

Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration







0

10

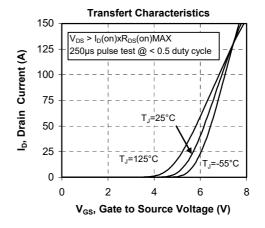
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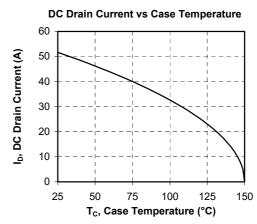
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I_D, Drain Current (A)

40

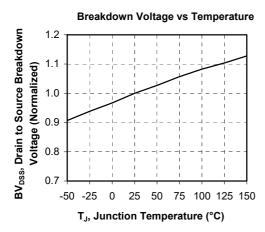
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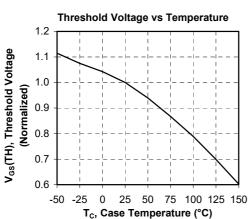


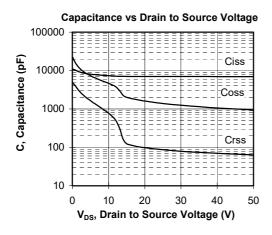


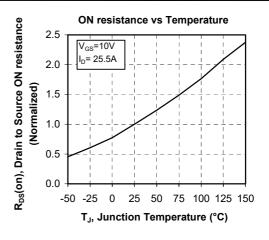
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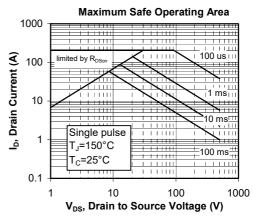


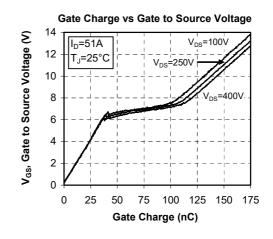




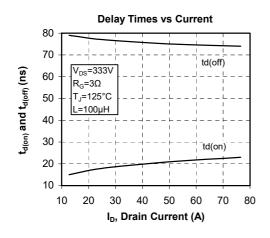


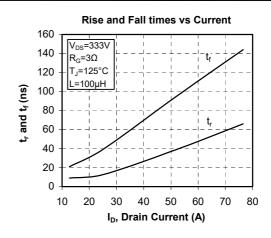


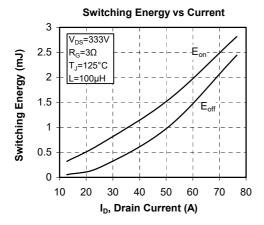


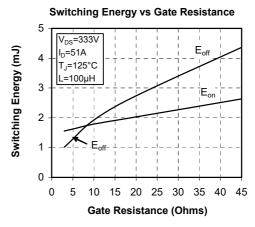


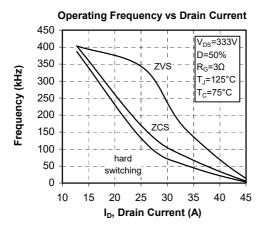


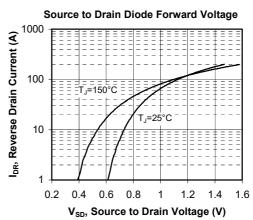














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